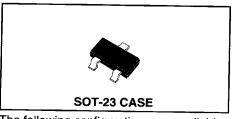
CMPD5001 CMPD5001S

HIGH CURRENT INDUCTIVE LOAD SWITCHING DIODE



The following configurations are available:

CMPD5001

SINGLE

CMPD5001S

DUAL, IN SERIES

MAXIMUM RATINGS (TA=25°C)

Central [™]
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD5001 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for switching inductive load applications requiring extremely high current capability.

MARKING CODE: DA2
MARKING CODE: D49

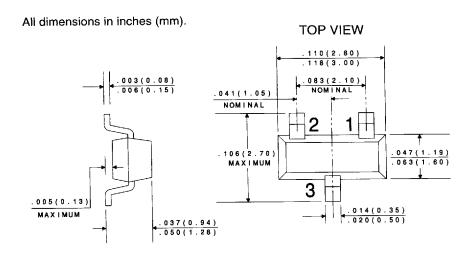
	SYMBOL		UNITS
Continuous Reverse Voltage	V_{R}	120	V
Continuous Forward Current	l _E	400	mA
Peak Repetitive Forward Current	I _{FRM}	800	mA
Peak Repetitive Reverse Current	RRM	600	mA
Forward Surge Current, tp=1 μs	FSM	6000	mA
Forward Surge Current, tp=1 s	^I FSM	1500	mA
Power Dissipation	PD	350	mW
Operating and Storage	J		*****
Junction Temperature	T_{J}, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ.IA	357	°C/W

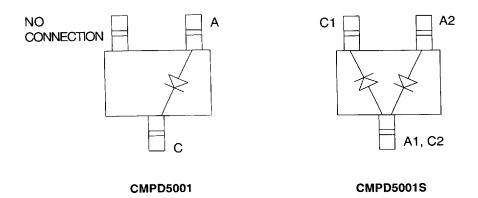
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
B_VR	I _R =1.0mA	120	175	V
^l R	V _R =90V		100	пA
^l R	V _R =90V, T _A =150 ^o C		100	μΑ
V _F	I _F =10mA		0.75	·v
V _F	I _F =50mA		0.84	٧
٧ _F	I _F =100mA		0.90	٧
٧ _F	I _F =200mA		1.00	V

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SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
٧ _E	I _F =400mA		1.25	V
Ст	√ _R =0, f=1 MHz		35	pF
t _{rr}	$I_{E}=I_{R}=30$ mA, RECOV. TO 1.0mA, $R_{L}=100\Omega$		60	ns
trr	$I_{\text{F}}=I_{\text{R}}=10\text{mA}$, RECOV. TO 1.0mA, $R_{\text{L}}=100\Omega$		50	ns





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R2